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شبكة المعلومات الجامعية التوثيق الالكتروني والميكرو فيلم



شبكة المعلومات الجامعية

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التوثيق الالكتروني والميكرو فيلم

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MANSOURA UNIVERSITY
FACULTY OF ENGINEERING
DEPARTMENT OF ELECTRONIC
AND COMMUNICATIONS ENGINEERING

Chouf

Performance of Optical Receiver Using Avalanche Diodes

A Thesis

**Submitted in partial Fulfillment for the Degree of
Master of Science**

**In
ELECTRONIC AND COMMUNICATIONS
ENGINEERING**

**By
Eng.
Hisham M. Sheleel Ali**

**Registered : March, 1997
Approved: July 2001**

PERFORMANCE
OF OPTICAL
RECEIVER USING
AVALANCHE
DIODES


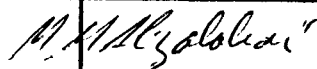
SUPERVISORS

Thesis Title :

Performance of Optical Receiver Using Avalanche Diodes

Supervisors :

Name	Position
1. Assoc. Prof. Dr. Roshdy Abu El Azaïem Abd El Rassoul	Assoc. Prof. At Electronic and Communication Engineering Dept. Faculty of Engineering Mansoura University
2. Prof. Dr. Mahmoud Mohammed El Zalabani	Assoc. Prof. At Electronic and Communication Engineering Dept. Faculty of Engineering Mansoura University

Name	Signature
1. Assoc. Prof. Dr. Roshdy A Abu El Azaïem. Abd El Rassoul	
2. Prof. Dr. Mahmoud Mohammed El Zalabani	

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2. Prof. Dr. Mahmoud Mohammed El Zalabani	

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List of Symbols

B	electrical bandwidth (post detection)
c	velocity of light
D_n	electron diffusion coefficient
D_p	hole diffusion coefficient
e	magnitude of the electron charge
ξ	electric field
E_{ie}	electron ionization energy
E_{ih}	hole ionization energy
E_g	bandgap energy
h	normalized Planck's constant
k_B	boltzmann constant
L_n	diffusion length for electrons
L_p	diffusion length for holes
n	electron concentration in the conduction band
n_i	intrinsic electron concentration in the conduction band
N_c (E)	effective density of states in the conduction band
N_v (E)	effective density of states in the valence band
R_L	load resistance
SNR	signal to noise ratio
v	velocity of the electron
V_{bi}	built-in voltage
V_r (V_f)	reverse (forward) bias voltage in a diode
W_n (W_p)	depletion region edge on the n-side (p-side) of a p-n junction
W	depletion region width
α_{imp}	impact ionization coefficient for electrons
β_{imp}	impact ionization coefficient for holes
ε_o	free space permittivity
μ_n (μ_p)	electron (hole) mobility
λ_c	cutoff wavelength of a detector
η_Q	quantum efficiency of a detector

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